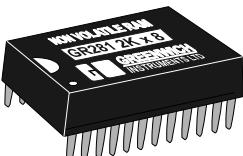


GR281 (2K x 8) NON-VOLATILE RAM



DESCRIPTION

The GR281 is a 2048 word by 8 bits (2K x 8) non-volatile CMOS Static Ram, fabricated from advanced silicon gate CMOS technology and a high reliability lithium power cell.

The pin-out of the GR281 conforms to the JEDEC standards and is fully compatible with normal static RAM.

The power down circuit is fully automatic and is referenced at 4.5 volts. At this point the GR281 is write protected by an internal inhibit function for Data Protection and the memory contents are retained by the lithium power source.

Power down is very fast, this being essential for data integrity, taking a maximum of 15 μ s (15 microseconds) to power down from 5 volts to 0 volts. This is much faster than system power failure conditions. Therefore there are no special conditions required when installing the GR281.

The GR281 can, without external power, retain data almost indefinitely. The limiting factor will be the shelf life of the lithium cell, which is typically ten years. It is possible that this figure may be extended in view of the extremely light duty imposed upon the cell.

APPLICATION

When powered down, the GR281 is transportable and data can be moved from system to system. Being pin compatible with 2716 EPROM makes it ideal for programme development, data collection in data loggers, programme changes in process control, automation and robotics and user definable lookup tables, etc.

DISPOSAL INSTRUCTIONS

Do not dispose of non-volatile memory devices by incineration or crushing. Devices may be returned carriage paid to Greenwich Instruments Ltd., for disposal.

UK

Greenwich Instruments Ltd.,
Meridian House, Park Road,
Swanley, Kent. BR8 8AH
Tele: 08700 505 404
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ABSOLUTE MAXIMUM RATINGS

Symbol	Min	Max	Units
Vdd	-0.3	7.0	Volts
Vi/o	-0.3	Vdd +0.3	Volts
Temp	-20	+70	deg. C

OPERATING CONDITIONS

Symbol	Min	Typ	Max	Unit
Vdd	4.75	5.0	5.5	Volts
Vin (1)	2.2			Volts
Vin (0)	-0.3		0.8	Volts
Iin (any other pin)	-1.0	+1.0	μ A	μ A
Vout (1)(Iout = -1mA)	2.4			Volts
Vout (0)(Iout = +2mA)		0.4		Volts
Idd (Active)		25		mA
Idd (Deselected)		1.0		mA
Cycle		100		nS
Cin (any pin)		10		pF

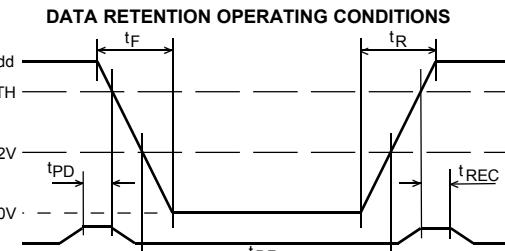
OPERATING MODE

CE	OE	WR	MODE	OUTPUT	Idd
H	X	X	Unsel.	Hi-Z	Standby
L	H	H	Unsel.	Hi-Z	Active
L	L	H	Read	Dout	Active
L	X	L	Write	Din	Active

PIN CONNECTIONS

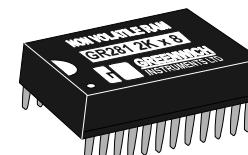
A7	24	Vdd	Pin	Function
A6	23	A8	A0-A10	Address I/P's
A5	22	A9	D0-D7	Data in/out
A4	21	WR	OE	Output Enable
A3	20	OE	CE	Chip Enable
A2	19	A10	WR	Write Input
A1	18	CE	WR	
A0	17	D7	Vdd	+5Volt Power
D0	16	D6	GND	Ground
D1	15	D5		
D2	14	D4		
GND	13	D3		

PIN DESIGNATIONS



Symbol	Parameter	Min	Typ	Max	Units
Vdd	Operating supply voltage	4.75	5.0	5.50	Volts
VTH	Data retention voltage		4.5		Volts
t_F	Vdd slew to 0V	15			μ s
t_R	Vdd slew 0V to 5.0V	15			μ s
t_{REC}	CE to O/P valid from power up		15		μ s
t_{DR}	Data retention time		10		Years
t_{PD}	CE at Vin(1) before power down	0			μ s

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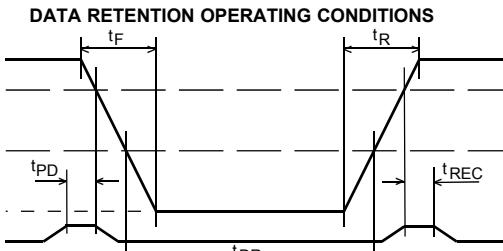
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H	X	X	Unsel.	Hi-Z	Standby
L	H	H	Unsel.	Hi-Z	Active
L	L	H	Read	Dout	Active
L	X	L	Write	Din	Active

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A1	18	CE	WR	OE	Function
A2	19	WR	A10	A0-A10	Address I/P's
A3	20	OE	D0-D7	D0-D7	Data in/out
A4	21	CE	OE	D9-D17	Output Enable
A5	22	WR	CE	A9-A17	Chip Enable
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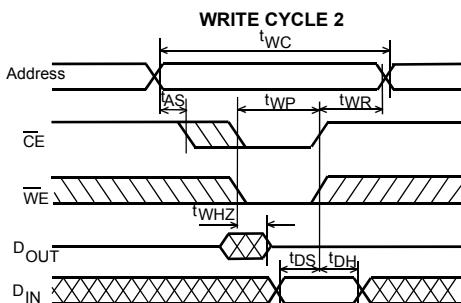
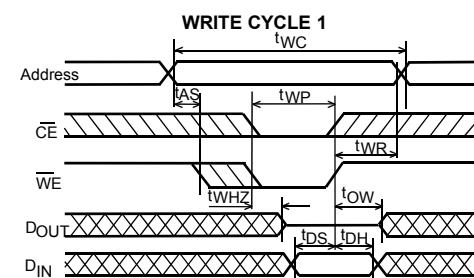
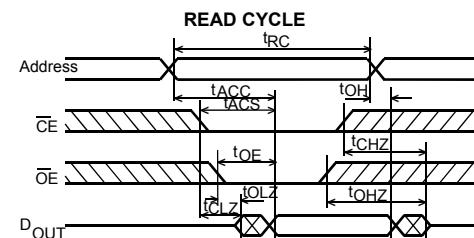
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**GR281 (2K x 8)
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TIMING (nS-nano seconds)

Symbol	Parameter	100nS
	Min	Max
t _{RC}	Read cycle time	100
t _{ACC}	Access time	100
t _{ACS}	CE to output valid	100
t _{OE}	OE to output valid	40
t _{CLZ}	CE to output active	10
t _{OLZ}	OE to output active	10
t _{OH}	Output hold time	10
t _{CHZ}	CE to output disable	40
t _{OHZ}	OE to output disable	40

Symbol	Parameter	100nS
	Min	Max
t _{WC}	Write cycle time	100
t _{WP}	Write pulse width	60
t _{AS}	Address setup time	0
t _{WR}	Write recovery time	10
t _{WHZ}	WR to output disable	30
t _{OW}	Output active from WR	10
t _{DS}	Data setup time	30
t _{DH}	Data HOLD TIME	10

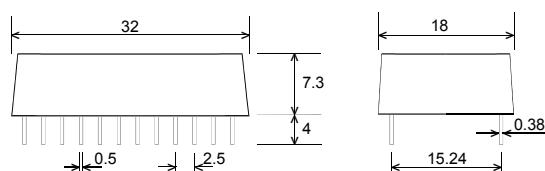
Notes

- WE must be high during address transitions.
- A Write occurs during the overlap of active CE and a low WE.
- WE is high for a read cycle.

REPLACES

2016., 6116., 8416., 5517., 4016., 2128., 5128., PD446., 8128., 4802., 5116., etc.

DIMENSIONS (mm)

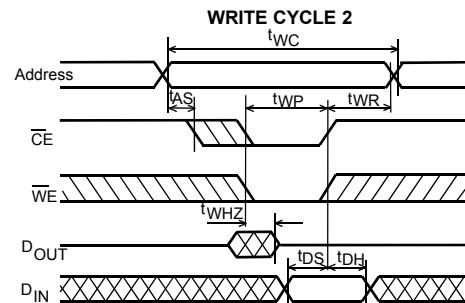
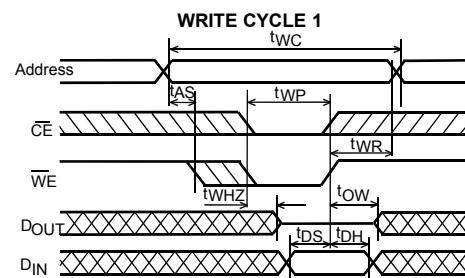
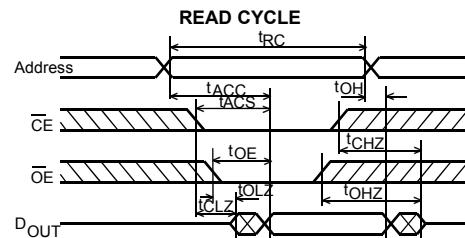


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ISSUE 4 OCT 2005

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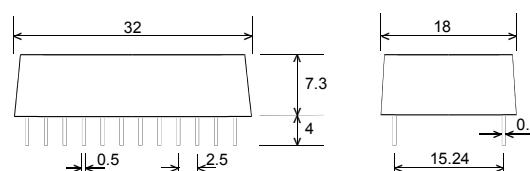
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